



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Low Gate Resistance
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

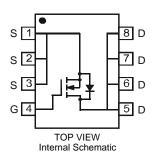
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)

SO-8



TOP VIEW



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 85°C	I _D	10 6	А
Pulsed Drain Current (Note 4)		I _{DM}	60	Α	
Avalanche Current (Notes 4 & 5)		I _{AR}	16	Α	
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.1mH		E _{AR}	12.8	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_{D}	1.42	W
Thermal Resistance, Junction to Ambient @Ta = 25°C (Note 3)	$R_{\theta JA}$	88.4	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
 Device mounted on FR-4 substrate PC board with minimum recommended pad layout in a still air environment @ T_A = 25°C. The value in any given application depends on the user's specific board design.

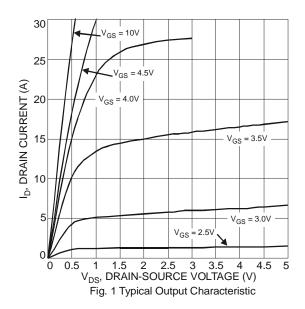
 4. Repetitive rating, pulse width limited by junction temperature.
- 5. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C

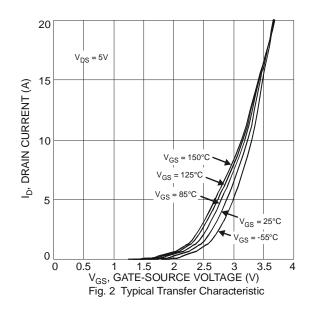


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)		-					
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)		-					
Gate Threshold Voltage	V _{GS(th)}	1.0	1.45	2.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Р	-	15 25	23 33	mΩ	$V_{GS} = 10V, I_{D} = 10A$	
Static Drain-Source On-Resistance	R _{DS (ON)}					$V_{GS} = 4.5V, I_D = 7.5A$	
Forward Transfer Admittance	Y _{fs}	-	2.5	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	V_{SD}	-	0.69	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)	-						
Input Capacitance	C _{iss}	-	478.9	-	pF	151/1/ 01/	
Output Capacitance	Coss	-	96.7	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	61.4	-	pF	1 = 1.000112	
Gate Resistance	Rg	0.4	1.1	1.6	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qq	-	5.0	8	0		
Total Gate Charge (V _{GS} = 10V)	Qq	-	10.5	17	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 10A	
Gate-Source Charge	Q _{gs}	-	1.8	-	nC		
Gate-Drain Charge	Q_{gd}	-	1.6	-	nC	1	
Turn-On Delay Time	t _{D(on)}	-	2.9	-	ns		
Turn-On Rise Time	t _r	-	7.9	-	ns	$V_{GS} = 10V, V_{DS} = 15V,$	
Turn-Off Delay Time	t _{D(off)}	-	14.6	-	ns	$R_G = 3\Omega$, $R_L = 1.5\Omega$	
Turn-Off Fall Time	t _f	-	3.1	-	ns	;	

Notes:

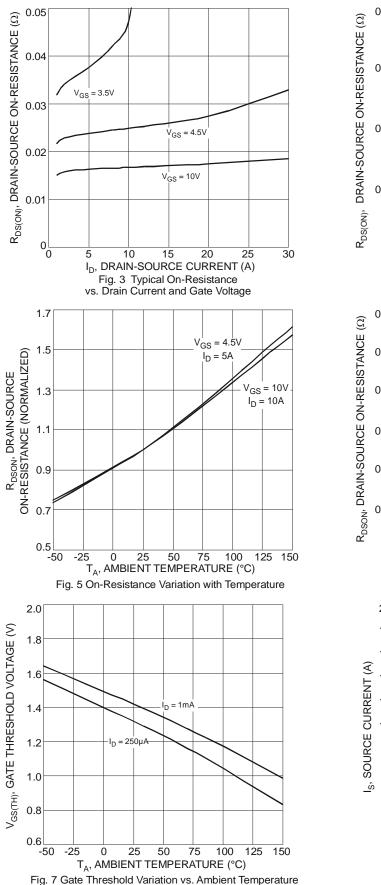


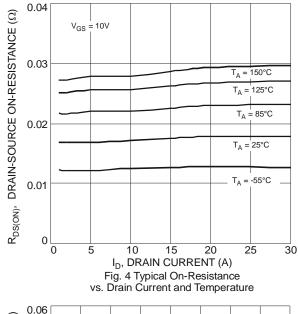


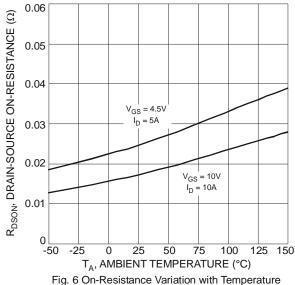
^{6.} Short duration pulse test used to minimize self-heating effect.

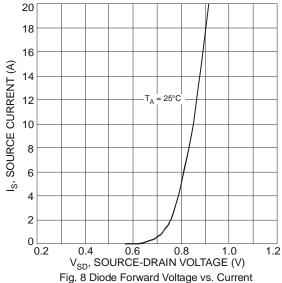
^{7.} Guaranteed by design. Not subject to production testing.



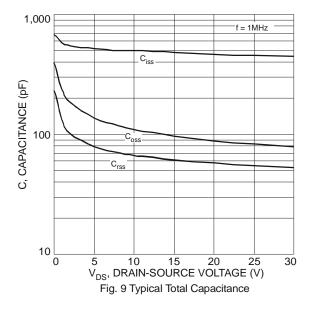


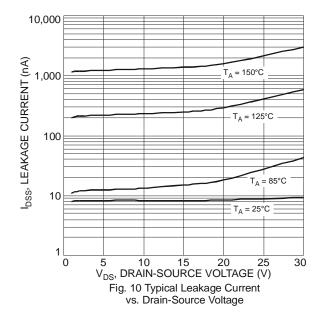


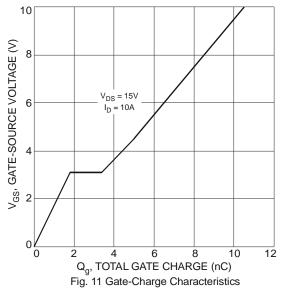


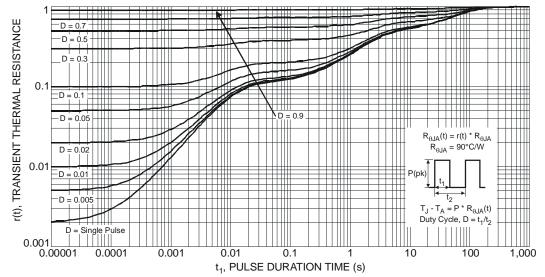












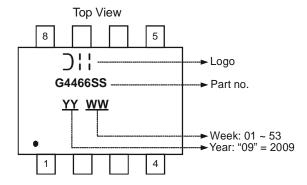


Ordering Information (Note 8)

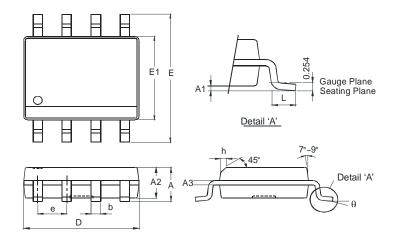
Part Number	Case	Packaging
DMG4466SSS-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

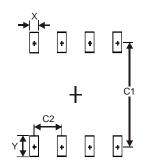


Package Outline Dimensions



SO-8				
Dim	Min	Max		
Α	-	1.75		
A 1	0.10	0.20		
A2	1.30	1.50		
А3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
٦	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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